

MAX32670

High Reliability, Ultra-Low Power Microcontroller Powered by Arm Cortex M4 Processor with FPU for Industrial and IoT

General Description

In the Darwin family, the MAX32670 is an ultra-low power, cost-effective, high reliability 32-bit microcontroller enabling designs with complex sensor processing without compromising battery life. It combines a flexible and versatile power management unit with the powerful Arm® Cortex®-M4 processor with floating point unit (FPU). The MAX32670 also offers legacy designs an easy and cost optimal upgrade path from 8- or 16-bit microcontrollers.

The device integrates up to 384KB of flash and 160KB of SRAM to accommodate application and sensor code. Error correction coding (ECC), capable of single error correction and double error detection (SEC-DED), is implemented over the entire flash, RAM, and cache to ensure ultra-reliable code execution for demanding applications. Additional features such as the two windowed watchdog timers with fully flexible and independent clocking have been added to further enhance reliable operation. Brown-out detection ensures proper operation during power-down and power-up events and unexpected supply transients.

Multiple high-speed peripherals such as 3.4MHz I²C, 50MHz SPI, and 4MBAUD UARTs are included to maximize communication bandwidth. In addition, a low-power UART is available for operation in the lowest power sleep modes to facilitate wakeup on activity without any loss of data. A total of six timers with I/O capability are provided, including two low-power timers to enable pulse counting, capture/compare and PWM generation even in the lowest power sleep modes. The device packs all this capability in tiny form factors: 5mm x 5mm 40-pin TQFN-EP and 1.7mm x 2.2mm 24-bump WLP packages.

Applications

- Smart Sensor Controller
- Industrial Sensors
- Optical Communication Modules
- Secure Radio Modem Controller
- Battery-Powered Medical Devices
- System Housekeeping Controller
- Algorithm Coprocessor

Ordering Information appears at end of data sheet.

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Benefits and Features

- High-Efficiency Microcontroller for Low Power, High Reliability Devices
 - Arm Cortex-M4 Core with FPU Up to 100MHz
 - 384KB Flash Memory with Error Correction
 - 160KB SRAM (128KB with ECC Enabled), Optionally Preserved in Lowest Power Modes
 - 16KB Unified Cache with ECC
 - UART Bootloader
 - Dual or Single-Supply Operation
 - Ultra-Low 0.9-1.1V V_{CORE} Supply Voltage
 - Internal LDO Operation from Single Supply 1.7V to 3.6V
 - Wide Operating Temperature: -40°C to +105°C
- Flexible Clocking Schemes
 - Internal High Speed 100MHz Oscillator
 - Internal Low Power 7.3728MHz and Ultra-Low Power 80kHz Oscillators
 - 14MHz to 32MHz Oscillator (External Crystal Required)
 - 32.768kHz Oscillator (External Crystal Required)
 - External Clock Input for the Core
 - External Clock Input for the LPUART and LPTMR
- Power Management Maximizes Uptime for Battery Applications
 - 44µA/MHz Active at 0.9V Up to 12MHz
 - 50µA/MHz Active at 1.1V Up to 100MHz
 - 2.6µA Full Memory Retention Power in Backup Mode at V_{DD} = 1.8V
 - 350nA Ultra-Low Power RTC at V_{DD} = 1.8V
 - Wake from LPUART or LPTMR
- Optimal Peripheral Mix Provides Platform Scalability
 - Up to 31 General-Purpose I/O Pins
 - Up to Three SPI Master/Slave (Up to 50MHz)
 - Up to Three 4-Wire UART (Up to 4MBAUD)
 - One Low Power UART (LPUART)
 - Up to Three I²C Master/Slave 3.4Mbps High Speed
 - Eight-Channel Standard DMA Controller
 - Up to Four 32-Bit Timers (TMR)
 - Up to Two Low Power 32-Bit Timers (LPTMR)
 - Two Windowed Watchdog Timers
 - One I²S Slave for Digital Audio Interface
- Security and Integrity
 - Available Secure Boot
 - AES 128/192/256 Hardware Acceleration Engine
 - TRNG Compliant to SP800-90B
 - 32-Bit CRC Acceleration Engine

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Simplified Block Diagram

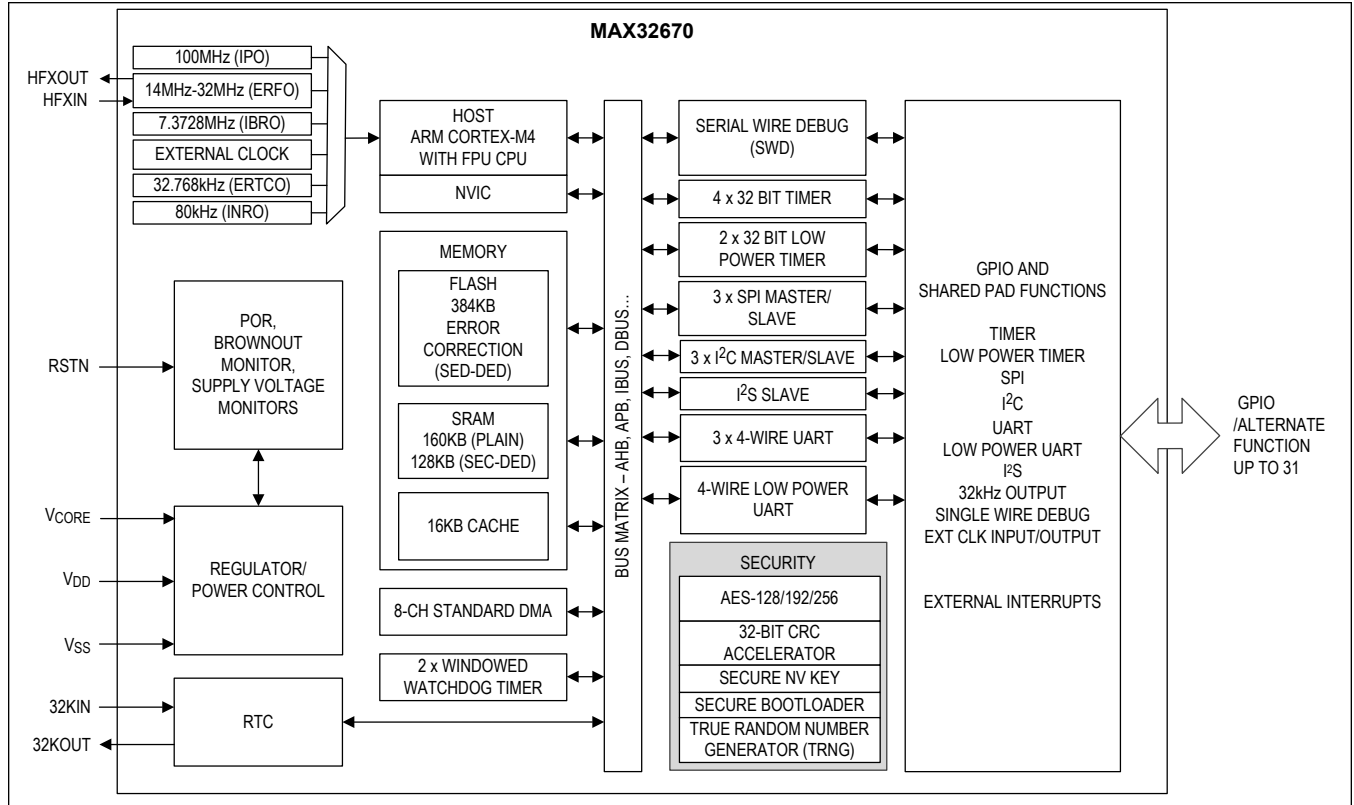


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Absolute Maximum Ratings

(All voltages with respect to V_{SS} , unless otherwise noted.)	Output Current (source) by Any GPIO Pin	-25mA
V_{CORE}	Continuous Package Power Dissipation 40 TQFN-EP (multilayer board) $T_A = +70^\circ\text{C}$ (derate $35.7\text{mW}/^\circ\text{C}$ above $+70^\circ\text{C}$)	2857.10mW
V_{DD}	Operating Temperature Range	-40°C to $+105^\circ\text{C}$
32KIN, 32KOUT, HFXIN, HFXOUT	Storage Temperature Range	-65°C to $+150^\circ\text{C}$
RSTN, GPIO	Soldering Temperature (reflow)	$+260^\circ\text{C}$
Total Current into All GPIO Combined (sink)		100mA
V_{SS}		100mA
Output Current (sink) by Any GPIO Pin		25mA

All voltages with respect to V_{SS} : (All voltages with respect to V_{SS} , unless otherwise noted.)

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Package Information

40 TQFN-EP

Package Code	T4055+1
Outline Number	21-0140
Land Pattern Number	90-0016
Thermal Resistance, Single-Layer Board:	
Junction to Ambient (θ_{JA})	45°C/W
Junction to Case (θ_{JC})	2 °C/W
Thermal Resistance, Four-Layer Board:	
Junction to Ambient (θ_{JA})	28°C/W
Junction to Case (θ_{JC})	2°C/W

For the latest package outline information and land patterns (footprints), go to www.maximintegrated.com/packages. Note that a "+", "#", or "-" in the package code indicates RoHS status only. Package drawings may show a different suffix character, but the drawing pertains to the package regardless of RoHS status.

Package thermal resistances were obtained using the method described in JEDEC specification JESD51-7, using a four-layer board. For detailed information on package thermal considerations, refer to www.maximintegrated.com/thermal-tutorial.

Electrical Characteristics

(Limits are 100% tested at $T_A = +25^\circ\text{C}$ and $T_A = +105^\circ\text{C}$. Limits over the operating temperature range and relevant supply voltage range are guaranteed by design and characterization. Specifications marked GBD are guaranteed by design and not production tested. Specifications to the minimum operating temperature are guaranteed by design and are not production tested.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	
POWER / BOTH SINGLE-SUPPLY OPERATION AND DUAL-SUPPLY OPERATION							
Supply Voltage	V_{DD}		1.71	1.8	3.63	V	
Supply Voltage, Core	V_{CORE}	Dual-supply operation	OVR = [00]	0.855	0.9	0.945	V
			OVR = [01]	0.95	1.0	1.05	
			Default OVR = [10]	1.045	1.1	1.155	
		No power supply connection for single supply operation		—			
Power-Fail Reset Voltage	V_{RST}	Monitors V_{DD}	1.58		1.71	V	
		Monitors V_{CORE} during dual-supply operation	0.77		0.845		

Electrical Characteristics (continued)

(Limits are 100% tested at $T_A = +25^\circ\text{C}$ and $T_A = +105^\circ\text{C}$. Limits over the operating temperature range and relevant supply voltage range are guaranteed by design and characterization. Specifications marked GBD are guaranteed by design and not production tested. Specifications to the minimum operating temperature are guaranteed by design and are not production tested.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Power-On Reset Voltage	V_{POR}	Monitors V_{DD}		1.4		V
		Monitors V_{CORE} during dual supply operation		0.65		

Electrical Characteristics (continued)

(Limits are 100% tested at T_A = +25°C and T_A = +105°C. Limits over the operating temperature range and relevant supply voltage range are guaranteed by design and characterization. Specifications marked GBD are guaranteed by design and not production tested. Specifications to the minimum operating temperature are guaranteed by design and are not production tested.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
POWER / SINGLE-SUPPLY OPERATION (V_{DD} ONLY)						
V _{DD} Current Active Mode	I _{DD_DACTS}	Dynamic, IPO enabled, total current into V _{DD} pin, V _{DD} = 3.3V, CPU in Active mode, executing Coremark, ECC disabled, inputs tied to V _{SS} or V _{DD} , outputs source/sink 0mA	OVR = [10], internal regulator set to 1.1V, f _{sys_clk(MAX)} = 100MHz		64.5	μA/MHz
			OVR = [01], internal regulator set to 1.0V, f _{sys_clk(MAX)} = 50MHz		62.5	
			OVR = [00], internal regulator set to 0.9V, f _{sys_clk(MAX)} = 12MHz		59.5	
		Dynamic, IPO enabled, total current into V _{DD} pin, V _{DD} = 1.8V, CPU in Active mode, executing Coremark, ECC disabled, inputs tied to V _{SS} or V _{DD} , outputs source/sink 0mA	OVR = [10], internal regulator set to 1.1V, f _{sys_clk(MAX)} = 100MHz		64.2	
			OVR = [01], Internal regulator set to 1.0V, f _{sys_clk(MAX)} = 50MHz		62.1	
			OVR = [00], internal regulator set to 0.9V, f _{sys_clk(MAX)} = 12MHz		59.1	
		Dynamic, IPO enabled, total current into V _{DD} pin, V _{DD} = 3.3V, CPU in Active mode, executing While(1), ECC disabled, inputs tied to V _{SS} or V _{DD} , outputs source/sink 0mA	OVR = [10], internal regulator set to 1.1V, f _{sys_clk(MAX)} = 100MHz		49.4	
			OVR = [01], internal regulator set to 1.0V, f _{sys_clk(MAX)} = 50MHz		47	
			OVR = [00], internal regulator set to 0.9V, f _{sys_clk(MAX)} = 12MHz		44.1	

Electrical Characteristics (continued)

(Limits are 100% tested at T_A = +25°C and T_A = +105°C. Limits over the operating temperature range and relevant supply voltage range are guaranteed by design and characterization. Specifications marked GBD are guaranteed by design and not production tested. Specifications to the minimum operating temperature are guaranteed by design and are not production tested.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	
		Dynamic, IPO enabled, total current into V _{DD} pin, V _{DD} = 1.8V, CPU in Active mode, executing While(1), ECC disabled, inputs tied to V _{SS} or V _{DD} , outputs source/sink 0mA	OVR = [10], internal regulator set to 1.1V, f _{SYS_CLK(MAX)} = 100MHz		49.3		
			OVR = [01], internal regulator set to 1.0V, f _{SYS_CLK(MAX)} = 50MHz		46.7		
			OVR = [00], internal regulator set to 0.9V, f _{SYS_CLK(MAX)} = 12MHz		44.1		
	I _{DD_FACTS}	Fixed, IPO enabled, total current into V _{DD} pin, V _{DD} = 3.3V, CPU in Active mode 0MHz execution, ECC disabled, inputs tied to V _{SS} or V _{DD} , outputs source/sink 0mA	OVR = [10], internal regulator set to 1.1V		796		μA
			OVR = [01], internal regulator set to 1.0V		647		
			OVR = [00], internal regulator set to 0.9V		475		
		Fixed, IPO enabled, total current into V _{DD} pin, V _{DD} = 1.8V, CPU in Active mode 0MHz execution, ECC disabled, inputs tied to V _{SS} or V _{DD} , outputs source/sink 0mA	OVR = [10], internal regulator set to 1.1V		762		
			OVR = [01], internal regulator set to 1.0V		620		
			OVR = [00], internal regulator set to 0.9V		450		

Electrical Characteristics (continued)

(Limits are 100% tested at $T_A = +25^\circ\text{C}$ and $T_A = +105^\circ\text{C}$. Limits over the operating temperature range and relevant supply voltage range are guaranteed by design and characterization. Specifications marked GBD are guaranteed by design and not production tested. Specifications to the minimum operating temperature are guaranteed by design and are not production tested.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	
V _{DD} Current Sleep Mode	I _{DD_DSLPS}	Dynamic, IPO enabled, total current into V _{DD} pin, V _{DD} = 3.3V, CPU in Sleep mode, ECC disabled, standard DMA with two channels active, inputs tied to V _{SS} or V _{DD} , outputs source/sink 0mA	OVR = [10], internal regulator set to 1.1V		39.2		μA/MHz
			OVR = [01], internal regulator set to 1.0V, f _{SYS_CLK(MAX)} = 50MHz		37.5		
			OVR = [00], internal regulator set to 0.9V, f _{SYS_CLK(MAX)} = 12MHz		36.1		
		Dynamic, IPO enabled, total current into V _{DD} pin, V _{DD} = 1.8V, CPU in Sleep mode, ECC disabled, standard DMA with two channels active, inputs tied to V _{SS} or V _{DD} , outputs source/sink 0mA	OVR = [10], internal regulator set to 1.1V, f _{SYS_CLK(MAX)} = 100MHz		39.2		
			OVR = [01], internal regulator set to 1.0V, f _{SYS_CLK(MAX)} = 50MHz		37.5		
			OVR = [00], internal regulator set to 0.9V, f _{SYS_CLK(MAX)} = 12MHz		36.4		
	Dynamic, IPO enabled, total current into V _{DD} pin, V _{DD} = 3.3V, CPU in Sleep mode, ECC disabled, DMA disabled, inputs tied to V _{SS} or V _{DD} , outputs source/sink 0mA	OVR = [10], internal regulator set to 1.1V, f _{SYS_CLK(MAX)} = 100MHz		21.1			
		OVR = [01], internal regulator set to 1.0V, f _{SYS_CLK(MAX)} = 50MHz		19			
		OVR = [00], internal regulator set to 0.9V, f _{SYS_CLK(MAX)} = 12MHz		17.2			

Electrical Characteristics (continued)

(Limits are 100% tested at T_A = +25°C and T_A = +105°C. Limits over the operating temperature range and relevant supply voltage range are guaranteed by design and characterization. Specifications marked GBD are guaranteed by design and not production tested. Specifications to the minimum operating temperature are guaranteed by design and are not production tested.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	
		Dynamic, IPO enabled, total current into V _{DD} pin, V _{DD} = 1.8V, CPU in Sleep mode, ECC disabled, DMA disabled, inputs tied to V _{SS} or V _{DD} , outputs source/sink 0mA	OVR = [10], internal regulator set to 1.1V, f _{SYS_CLK(MAX)} = 100MHz		21.2		
			OVR = [01], internal regulator set to 1.0V, f _{SYS_CLK(MAX)} = 50MHz		19.1		
			OVR = [00], internal regulator set to 0.9V, f _{SYS_CLK(MAX)} = 12MHz		17.3		
	I _{DD_FSLPS}	Fixed, IPO enabled, total current into V _{DD} pin, V _{DD} = 3.3V, CPU in Sleep mode, ECC disabled, inputs tied to V _{SS} or V _{DD} , outputs source/sink 0mA	OVR = [10], internal regulator set to 1.1V		796		μA
			OVR = [01], internal regulator set to 1.0V		647		
			OVR = [00], internal regulator set to 0.9V		475		
			OVR = [10], internal regulator set to 1.1V		762		
			OVR = [01], internal regulator set to 1.0V		620		
			OVR = [00], internal regulator set to 0.9V		450		
V _{DD} Fixed Current, DeepSleep Mode	I _{DD_FDSL}	Standby state with full data retention and 160KB SRAM retained	V _{DD} = 3.3V		4.0	μA	
			V _{DD} = 1.8V		3.6		

Electrical Characteristics (continued)

(Limits are 100% tested at $T_A = +25^\circ\text{C}$ and $T_A = +105^\circ\text{C}$. Limits over the operating temperature range and relevant supply voltage range are guaranteed by design and characterization. Specifications marked GBD are guaranteed by design and not production tested. Specifications to the minimum operating temperature are guaranteed by design and are not production tested.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
V_{DD} Fixed Current, Backup Mode	I_{DD_FBKUS}	$V_{DD} = 3.3\text{V}$, RTC disabled	0KB SRAM retained, retention regulator disabled		0.32	μA
			20KB SRAM retained		1.04	
			40KB SRAM retained		1.37	
			80KB SRAM retained		1.90	
			160KB SRAM retained		2.84	
		$V_{DD} = 1.8\text{V}$, RTC disabled	0KB SRAM retained, retention regulator disabled		0.11	
			20KB SRAM retained		0.77	
			40KB SRAM retained		1.14	
			80KB SRAM retained		1.68	
			160KB SRAM retained		2.64	
V_{DD} Fixed Current, Storage Mode	I_{DD_FSTOS}	$V_{DD} = 3.3\text{V}$		0.362	μA	
		$V_{DD} = 1.8\text{V}$		0.075		
Sleep Mode Resume Time	t_{SLP_ONS}			2.1	μs	
DeepSleep Mode Resume Time	t_{DSL_ONS}	$fast_wk_en = 1$		89	μs	
		$fast_wk_en = 0$		129		
Backup Mode Resume Time	t_{BKU_ONS}	Includes system initialization and ROM execution time		1.25	ms	
Storage Mode Resume Time	t_{STO_ONS}	Includes system initialization and ROM execution time		1.5	ms	

Electrical Characteristics (continued)

(Limits are 100% tested at $T_A = +25^\circ\text{C}$ and $T_A = +105^\circ\text{C}$. Limits over the operating temperature range and relevant supply voltage range are guaranteed by design and characterization. Specifications marked GBD are guaranteed by design and not production tested. Specifications to the minimum operating temperature are guaranteed by design and are not production tested.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
POWER / DUAL-SUPPLY OPERATION (V_{DD} AND V_{CORE})						
V_{CORE} Current, Active Mode	I_{CORE_DACTD}	Dynamic, IPO enabled, total current into V_{CORE} pin, CPU in Active mode, executing Coremark, ECC disabled, inputs tied to V_{SS} or V_{DD} , outputs source/sink 0mA	OVR = [10], $V_{CORE} = 1.1\text{V}$, $f_{SYS_CLK(MAX)} = 100\text{MHz}$		63.7	$\mu\text{A/MHz}$
			OVR = [01], $V_{CORE} = 1.0\text{V}$, $f_{SYS_CLK(MAX)} = 50\text{MHz}$		61.9	
			OVR = [00], $V_{CORE} = 0.9\text{V}$, $f_{SYS_CLK(MAX)} = 12\text{MHz}$		59.4	
		Dynamic, IPO enabled, total current into V_{CORE} pin, CPU in Active mode, executing While(1), ECC disabled, inputs tied to V_{SS} or V_{DD} , outputs source/sink 0mA	OVR = [10], $V_{CORE} = 1.1\text{V}$, $f_{SYS_CLK(MAX)} = 100\text{MHz}$		48.9	
			OVR = [01], $V_{CORE} = 1.0\text{V}$, $f_{SYS_CLK(MAX)} = 50\text{MHz}$		46.6	
			OVR = [00], $V_{CORE} = 0.9\text{V}$, $f_{SYS_CLK(MAX)} = 12\text{MHz}$		44.5	
	I_{CORE_FACTD}	Fixed, IPO enabled, total current into V_{CORE} pin, CPU in Active mode 0MHz execution, ECC disabled, inputs tied to V_{SS} or V_{DD} , outputs source/sink 0mA	OVR = [10], $V_{CORE} = 1.1\text{V}$		362	μA
			OVR = [01], $V_{CORE} = 1.0\text{V}$		217	
			OVR = [00], $V_{CORE} = 0.9\text{V}$		109	

Electrical Characteristics (continued)

(Limits are 100% tested at $T_A = +25^\circ\text{C}$ and $T_A = +105^\circ\text{C}$. Limits over the operating temperature range and relevant supply voltage range are guaranteed by design and characterization. Specifications marked GBD are guaranteed by design and not production tested. Specifications to the minimum operating temperature are guaranteed by design and are not production tested.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	
V _{DD} Current, Active Mode	I _{DD_DACTD}	Dynamic, IPO enabled, total current into V _{DD} pin, V _{DD} = 3.3V, CPU in Active mode, executing Coremark, ECC disabled, inputs tied to V _{SS} or V _{DD} , outputs source/sink 0mA	OVR = [10], f _{SYS_CLK(MAX)} = 100MHz		0.51		μA/MHz
		Dynamic, IPO enabled, total current into V _{DD} pin, V _{DD} = 3.3V, CPU in Active mode, executing Coremark, ECC disabled, inputs tied to V _{SS} or V _{DD} , outputs source/sink 0mA	OVR = [01], f _{SYS_CLK(MAX)} = 50MHz		0.51		
		Dynamic, IPO enabled, total current into V _{DD} pin, V _{DD} = 3.3V, CPU in Active mode, executing Coremark, ECC disabled, inputs tied to V _{SS} or V _{DD} , outputs source/sink 0mA	OVR = [00], f _{SYS_CLK(MAX)} = 12MHz		0.51		
		Dynamic, IPO enabled, total current into V _{DD} pin, V _{DD} = 1.8V, CPU in Active mode, executing Coremark, ECC disabled, inputs tied to V _{SS} or V _{DD} , outputs source/sink 0mA	OVR = [10], f _{SYS_CLK(MAX)} = 100MHz		0.23		
			OVR = [01], f _{SYS_CLK(MAX)} = 50MHz		0.23		
			OVR = [00], f _{SYS_CLK(MAX)} = 12MHz		0.23		

Electrical Characteristics (continued)

(Limits are 100% tested at T_A = +25°C and T_A = +105°C. Limits over the operating temperature range and relevant supply voltage range are guaranteed by design and characterization. Specifications marked GBD are guaranteed by design and not production tested. Specifications to the minimum operating temperature are guaranteed by design and are not production tested.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
		Dynamic, IPO enabled, total current into V _{DD} pin, V _{DD} = 3.3V, CPU in Active mode, executing While(1), ECC disabled, inputs tied to V _{SS} or V _{DD} , outputs source/sink 0mA	OVR = [10], f _{SYS_CLK(MAX)} = 100MHz		0.51	
			OVR = [01], f _{SYS_CLK(MAX)} = 50MHz		0.51	
			OVR = [00], f _{SYS_CLK(MAX)} = 12MHz		0.51	
		Dynamic, IPO enabled, total current into V _{DD} pin, V _{DD} = 1.8V, CPU in Active mode, executing While(1), ECC disabled, inputs tied to V _{SS} or V _{DD} , outputs source/sink 0mA	OVR = [10], f _{SYS_CLK(MAX)} = 100MHz		0.23	
			OVR = [01], f _{SYS_CLK(MAX)} = 50MHz		0.23	
			OVR = [00], f _{SYS_CLK(MAX)} = 12MHz		0.23	
	I _{DD_FACTD}	Fixed, IPO enabled, total current into V _{DD} pin, V _{DD} = 3.3V, CPU in Active mode 0MHz execution, ECC disabled, inputs tied to V _{SS} or V _{DD} , outputs source/sink 0mA	OVR = [10], V _{CORE} = 1.1V		367	
			OVR = [01], V _{CORE} = 1.0V		367	
			OVR = [00], V _{CORE} = 0.9V		307	
Fixed, IPO enabled, total current into V _{DD} pin, V _{DD} = 1.8V, CPU in Active mode 0MHz execution, ECC disabled, inputs tied to V _{SS} or V _{DD} , outputs source/sink 0mA			OVR = [10], V _{CORE} = 1.1V		350	
			OVR = [01], V _{CORE} = 1.0V		350	
			OVR = [00], V _{CORE} = 0.9V		290	

Electrical Characteristics (continued)

(Limits are 100% tested at $T_A = +25^{\circ}\text{C}$ and $T_A = +105^{\circ}\text{C}$. Limits over the operating temperature range and relevant supply voltage range are guaranteed by design and characterization. Specifications marked GBD are guaranteed by design and not production tested. Specifications to the minimum operating temperature are guaranteed by design and are not production tested.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
V _{CORE} Current, Sleep Mode	I _{CORE_DSLPD}	Dynamic, IPO enabled, total current into V _{CORE} pin, CPU in Sleep mode, ECC disabled, standard DMA with two channels active, inputs tied to V _{SS} or V _{DD} , outputs source/sink 0mA	OVR = [10], V _{CORE} = 1.1V, f _{SYS_CLK(MAX)} = 100MHz		39.2	μA/MHz
			OVR = [01], V _{CORE} = 1.0V, f _{SYS_CLK(MAX)} = 50MHz		37.5	
			OVR = [00], V _{CORE} = 0.9V, f _{SYS_CLK(MAX)} = 12MHz		37	
		Dynamic, IPO enabled, total current into V _{CORE} pin, CPU in Sleep mode, ECC disabled, DMA disabled, inputs tied to V _{SS} or V _{DD} , outputs source/sink 0mA	OVR = [10], V _{CORE} = 1.1V, f _{SYS_CLK(MAX)} = 100MHz		21.1	
			OVR = [01], V _{CORE} = 1.0V, f _{SYS_CLK(MAX)} = 50MHz		19.2	
			OVR = [00], V _{CORE} = 0.9V, f _{SYS_CLK(MAX)} = 12MHz		17.9	
	I _{CORE_FSLPD}	Fixed, IPO enabled, total current into V _{CORE} pin, CPU in Sleep mode, ECC disabled, inputs tied to V _{SS} or V _{DD} , outputs source/sink 0mA	OVR [10], V _{CORE} = 1.1V		362	μA
			OVR [01], V _{CORE} = 1.0V		217	
			OVR [00], V _{CORE} = 0.9V		109	

Electrical Characteristics (continued)

(Limits are 100% tested at T_A = +25°C and T_A = +105°C. Limits over the operating temperature range and relevant supply voltage range are guaranteed by design and characterization. Specifications marked GBD are guaranteed by design and not production tested. Specifications to the minimum operating temperature are guaranteed by design and are not production tested.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
V _{DD} Current, Sleep Mode	I _{DD_DSLPD}	Dynamic, IPO enabled, total current into V _{DD} pin, V _{DD} = 3.3V, CPU in Sleep mode, ECC disabled, standard DMA with two channels active, inputs tied to V _{SS} or V _{DD} , outputs source/sink 0mA	OVR = [10], V _{CORE} = 1.1V, f _{SYS_CLK(MAX)} = 100MHz		0.001	μA/MHz
			OVR = [01], V _{CORE} = 1.0V, f _{SYS_CLK(MAX)} = 50MHz		0.001	
			OVR = [00], V _{CORE} = 0.9V, f _{SYS_CLK(MAX)} = 12MHz		0.001	
		Dynamic, IPO enabled, total current into V _{DD} pin, V _{DD} = 1.8V, CPU in Sleep mode, ECC disabled, standard DMA with two channels active, inputs tied to V _{SS} or V _{DD} , outputs source/sink 0mA	OVR = [10], V _{CORE} = 1.1V, f _{SYS_CLK(MAX)} = 100MHz		0.001	
			OVR = [01], V _{CORE} = 1.0V, f _{SYS_CLK(MAX)} = 50MHz		0.001	
			OVR = [00], V _{CORE} = 0.9V, f _{SYS_CLK(MAX)} = 12MHz		0.001	
	I _{DD_FSLPD}	Fixed, IPO enabled, total current into V _{DD} pin, V _{DD} = 3.3V, CPU in Sleep mode, ECC disabled, inputs tied to V _{SS} or V _{DD} , outputs source/sink 0mA	OVR = [10], V _{CORE} = 1.1V		367	μA
			OVR = [01], V _{CORE} = 1.0V		367	
			OVR = [00], V _{CORE} = 0.9V		307	
		Fixed, IPO enabled, total current into V _{DD} pin, V _{DD} = 1.8V, CPU in Sleep mode, ECC disabled, inputs tied to V _{SS} or V _{DD} , outputs source/sink 0mA	OVR = [10], V _{CORE} = 1.1V		350	
OVR = [01], V _{CORE} = 1.0V				350		
OVR = [00], V _{CORE} = 0.9V				290		

Electrical Characteristics (continued)

(Limits are 100% tested at $T_A = +25^\circ\text{C}$ and $T_A = +105^\circ\text{C}$. Limits over the operating temperature range and relevant supply voltage range are guaranteed by design and characterization. Specifications marked GBD are guaranteed by design and not production tested. Specifications to the minimum operating temperature are guaranteed by design and are not production tested.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
V_{CORE} Fixed Current, DeepSleep Mode	$I_{\text{CORE_FD}}\text{SLPD}$	$V_{\text{DD}} = 3.3\text{V}, V_{\text{CORE}} = 1.1\text{V}$		10		μA
		$V_{\text{DD}} = 3.3\text{V}, V_{\text{CORE}} = 0.855\text{V}$		3.8		
		$V_{\text{DD}} = 1.8\text{V}, V_{\text{CORE}} = 1.1\text{V}$		10		
		$V_{\text{DD}} = 1.8\text{V}, V_{\text{CORE}} = 0.855\text{V}$		3.8		
V_{DD} Fixed Current, DeepSleep Mode	$I_{\text{DD_FD}}\text{SLPD}$	$V_{\text{DD}} = 3.3\text{V}, V_{\text{CORE}} = 1.1\text{V}$		0.34		μA
		$V_{\text{DD}} = 3.3\text{V}, V_{\text{CORE}} = 0.855\text{V}$		0.34		
		$V_{\text{DD}} = 1.8\text{V}, V_{\text{CORE}} = 1.1\text{V}$		0.08		
		$V_{\text{DD}} = 1.8\text{V}, V_{\text{CORE}} = 0.855\text{V}$		0.08		

Electrical Characteristics (continued)

(Limits are 100% tested at $T_A = +25^\circ\text{C}$ and $T_A = +105^\circ\text{C}$. Limits over the operating temperature range and relevant supply voltage range are guaranteed by design and characterization. Specifications marked GBD are guaranteed by design and not production tested. Specifications to the minimum operating temperature are guaranteed by design and are not production tested.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS		
V_{CORE} Fixed Current, Backup Mode	$I_{\text{CORE_FBKUD}}$	0KB SRAM retained, RTC disabled, retention regulator disabled	$V_{\text{DD}} = 3.3\text{V}$, $V_{\text{CORE}} = 1.1\text{V}$		0.225		μA	
			$V_{\text{DD}} = 3.3\text{V}$, $V_{\text{CORE}} = 0.855\text{V}$		0.13			
			$V_{\text{DD}} = 1.8\text{V}$, $V_{\text{CORE}} = 1.1\text{V}$		0.23			
			$V_{\text{DD}} = 1.8\text{V}$, $V_{\text{CORE}} = 0.855\text{V}$		0.14			
		20KB SRAM retained with RTC disabled	$V_{\text{DD}} = 3.3\text{V}$, $V_{\text{CORE}} = 1.1\text{V}$		1.256			
			$V_{\text{DD}} = 3.3\text{V}$, $V_{\text{CORE}} = 0.855\text{V}$		0.507			
			$V_{\text{DD}} = 1.8\text{V}$, $V_{\text{CORE}} = 1.1\text{V}$		1.256			
			$V_{\text{DD}} = 1.8\text{V}$, $V_{\text{CORE}} = 0.855\text{V}$		0.507			
		40KB SRAM retained with RTC disabled	$V_{\text{DD}} = 3.3\text{V}$, $V_{\text{CORE}} = 1.1\text{V}$		2.243			
			$V_{\text{DD}} = 3.3\text{V}$, $V_{\text{CORE}} = 0.855\text{V}$		0.877			
			$V_{\text{DD}} = 1.8\text{V}$, $V_{\text{CORE}} = 1.1\text{V}$		2.243			
			$V_{\text{DD}} = 1.8\text{V}$, $V_{\text{CORE}} = 0.855\text{V}$		0.877			
		80KB SRAM retained with RTC disabled	$V_{\text{DD}} = 3.3\text{V}$, $V_{\text{CORE}} = 1.1\text{V}$		3.97			
			$V_{\text{DD}} = 3.3\text{V}$, $V_{\text{CORE}} = 0.855\text{V}$		1.49			
			$V_{\text{DD}} = 1.8\text{V}$, $V_{\text{CORE}} = 1.1\text{V}$		3.97			
			$V_{\text{DD}} = 1.8\text{V}$, $V_{\text{CORE}} = 0.855\text{V}$		1.49			
		160KB SRAM retained with RTC disabled	$V_{\text{DD}} = 3.3\text{V}$, $V_{\text{CORE}} = 1.1\text{V}$		7.22			
			$V_{\text{DD}} = 3.3\text{V}$, $V_{\text{CORE}} = 0.855\text{V}$		2.61			
			$V_{\text{DD}} = 1.8\text{V}$, $V_{\text{CORE}} = 1.1\text{V}$		7.22			
			$V_{\text{DD}} = 1.8\text{V}$, $V_{\text{CORE}} = 0.855\text{V}$		2.61			

Electrical Characteristics (continued)

(Limits are 100% tested at $T_A = +25^\circ\text{C}$ and $T_A = +105^\circ\text{C}$. Limits over the operating temperature range and relevant supply voltage range are guaranteed by design and characterization. Specifications marked GBD are guaranteed by design and not production tested. Specifications to the minimum operating temperature are guaranteed by design and are not production tested.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
V_{DD} Fixed Current, Backup Mode	I_{DD_FBKUD}	0KB SRAM retained with RTC disabled, retention regulator disabled	$V_{DD} = 3.3\text{V},$ $V_{CORE} = 1.1\text{V}$		0.34	μA
			$V_{DD} = 3.3\text{V},$ $V_{CORE} = 0.855\text{V}$		0.34	
			$V_{DD} = 1.8\text{V},$ $V_{CORE} = 1.1\text{V}$		0.12	
			$V_{DD} = 1.8\text{V},$ $V_{CORE} = 0.855\text{V}$		0.12	
		20KB SRAM retained with RTC disabled	$V_{DD} = 3.3\text{V},$ $V_{CORE} = 1.1\text{V}$		0.32	
			$V_{DD} = 3.3\text{V},$ $V_{CORE} = 0.855\text{V}$		0.32	
			$V_{DD} = 1.8\text{V},$ $V_{CORE} = 1.1\text{V}$		0.108	
			$V_{DD} = 1.8\text{V},$ $V_{CORE} = 0.855\text{V}$		0.108	
		40KB SRAM retained with RTC disabled	$V_{DD} = 3.3\text{V},$ $V_{CORE} = 1.1\text{V}$		0.32	
			$V_{DD} = 3.3\text{V},$ $V_{CORE} = 0.855\text{V}$		0.108	
			$V_{DD} = 1.8\text{V},$ $V_{CORE} = 1.1\text{V}$		0.108	
			$V_{DD} = 1.8\text{V},$ $V_{CORE} = 0.855\text{V}$		0.108	
		80KB SRAM retained with RTC disabled	$V_{DD} = 3.3\text{V},$ $V_{CORE} = 1.1\text{V}$		0.32	
			$V_{DD} = 3.3\text{V},$ $V_{CORE} = 0.855\text{V}$		0.32	
			$V_{DD} = 1.8\text{V},$ $V_{CORE} = 1.1\text{V}$		0.108	
			$V_{DD} = 1.8\text{V},$ $V_{CORE} = 0.855\text{V}$		0.108	
		160KB SRAM retained with RTC disabled	$V_{DD} = 3.3\text{V},$ $V_{CORE} = 1.1\text{V}$		0.32	
			$V_{DD} = 3.3\text{V},$ $V_{CORE} = 0.855\text{V}$		0.32	
			$V_{DD} = 1.8\text{V},$ $V_{CORE} = 1.1\text{V}$		0.108	
			$V_{DD} = 1.8\text{V},$ $V_{CORE} = 0.855\text{V}$		0.108	

Electrical Characteristics (continued)

(Limits are 100% tested at $T_A = +25^\circ\text{C}$ and $T_A = +105^\circ\text{C}$. Limits over the operating temperature range and relevant supply voltage range are guaranteed by design and characterization. Specifications marked GBD are guaranteed by design and not production tested. Specifications to the minimum operating temperature are guaranteed by design and are not production tested.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
V_{CORE} Fixed Current, Storage Mode	$I_{\text{CORE_FSTOD}}$	$V_{\text{DD}} = 3.3\text{V}, V_{\text{CORE}} = 1.1\text{V}$		0.226		μA
		$V_{\text{DD}} = 3.3\text{V}, V_{\text{CORE}} = 0.855\text{V}$		0.112		
		$V_{\text{DD}} = 1.8\text{V}, V_{\text{CORE}} = 1.1\text{V}$		0.226		
		$V_{\text{DD}} = 1.8\text{V}, V_{\text{CORE}} = 0.855\text{V}$		0.112		
V_{DD} Fixed Current, Storage Mode	$I_{\text{DD_FSTOD}}$	$V_{\text{DD}} = 3.3\text{V}; V_{\text{CORE}} = 1.1\text{V}$		0.335		μA
		$V_{\text{DD}} = 3.3\text{V}; V_{\text{CORE}} = 0.855\text{V}$		0.335		
		$V_{\text{DD}} = 1.8\text{V}; V_{\text{CORE}} = 1.1\text{V}$		0.085		
		$V_{\text{DD}} = 1.8\text{V}; V_{\text{CORE}} = 0.855\text{V}$		0.085		
Sleep Mode Resume Time	$t_{\text{SLP_OND}}$			2.1		μs
DeepSleep Mode Resume Time	$t_{\text{DSL_OND}}$	$\text{fast_wk_en} = 1$		81		μs
		$\text{fast_wk_en} = 0$		129		μs
Backup Mode Resume Time	$t_{\text{BKU_OND}}$	Includes system initialization and ROM execution time		1.25		ms
Storage Mode Resume Time	$t_{\text{STO_OND}}$	Includes system initialization and ROM execution time		1.5		ms
GENERAL-PURPOSE I/O						
Input Low Voltage for All GPIO, RSTN	$V_{\text{IL_GPIO}}$	Pin configured as GPIO			$0.3 \times V_{\text{DD}}$	V
Input High Voltage for All GPIO, RSTN	$V_{\text{IH_GPIO}}$	Pin configured as GPIO	$0.7 \times V_{\text{DD}}$			V
Output Low Voltage for All GPIO Except P0.6, P0.7, P0.12, P0.13, P0.18, and P0.19	$V_{\text{OL_GPIO}}$	$V_{\text{DD}} = 1.71\text{V}, I_{\text{OL}} = 1\text{mA}, \text{DS}[1:0] = 00$ (Note 1)		0.2	0.4	V
		$V_{\text{DD}} = 1.71\text{V}, I_{\text{OL}} = 2\text{mA}, \text{DS}[1:0] = 10$ (Note 1)		0.2	0.4	
		$V_{\text{DD}} = 1.71\text{V}, I_{\text{OL}} = 4\text{mA}, \text{DS}[1:0] = 01$ (Note 1)		0.2	0.4	
		$V_{\text{DD}} = 1.71\text{V}, I_{\text{OL}} = 6\text{mA}, \text{DS}[1:0] = 11$ (Note 1)		0.2	0.4	
Output Low Voltage for GPIO P0.6, P0.7, P0.12, P0.13, P0.18, P0.19	$V_{\text{OL_I2C}}$	$V_{\text{DD}} = 1.71\text{V}, I_{\text{OL}} = 2\text{mA}, \text{DS} = 0$ (Note 1)		0.2	0.4	V
		$V_{\text{DD}} = 1.71\text{V}, I_{\text{OL}} = 10\text{mA}, \text{DS} = 1$ (Note 1)		0.2	0.4	
Output High Voltage for All GPIO Except P0.6, P0.7, P0.12, P0.13, P0.18, and P0.19	$V_{\text{OH_GPIO}}$	$V_{\text{DD}} = 1.71\text{V}, I_{\text{OH}} = 1\text{mA}, \text{DS}[1:0] = 00$ (Note 1)	$V_{\text{DD}} - 0.4$			V
		$V_{\text{DD}} = 1.71\text{V}, I_{\text{OH}} = 2\text{mA}, \text{DS}[1:0] = 10$ (Note 1)	$V_{\text{DD}} - 0.4$			
		$V_{\text{DD}} = 1.71\text{V}, I_{\text{OH}} = 4\text{mA}, \text{DS}[1:0] = 01$ (Note 1)	$V_{\text{DD}} - 0.4$			
		$V_{\text{DD}} = 1.71\text{V}, I_{\text{OH}} = 6\text{mA}, \text{DS}[1:0] = 11$ (Note 1)	$V_{\text{DD}} - 0.4$			

Electrical Characteristics (continued)

(Limits are 100% tested at $T_A = +25^\circ\text{C}$ and $T_A = +105^\circ\text{C}$. Limits over the operating temperature range and relevant supply voltage range are guaranteed by design and characterization. Specifications marked GBD are guaranteed by design and not production tested. Specifications to the minimum operating temperature are guaranteed by design and are not production tested.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Output High Voltage for GPIO P0.6, P0.7, P0.12, P0.13, P0.18, and P0.19	V_{OH_I2C}	$V_{DD} = 1.71\text{V}$, $I_{OH} = 2\text{mA}$, $DS = 0$ (Note 1)	$V_{DD} - 0.4$			V
		$V_{DD} = 1.71\text{V}$, $I_{OH} = 10\text{mA}$, $DS = 1$ (Note 1)	$V_{DD} - 0.4$			
Combined I_{OL} , All GPIO	I_{OL_TOTAL}				100	mA
Combined I_{OH} , All GPIO	I_{OH_TOTAL}		-100			mA
Input Hysteresis (Schmitt)	V_{IHYS}			300		mV
Input/Output Pin Capacitance for All Pins	C_{IO}			4		pF
Input Leakage Current Low	I_{IL}	$V_{IN} = 0\text{V}$, internal pullup disabled	-500		+500	nA
Input Leakage Current High	I_{IH}	$V_{IN} = 3.6\text{V}$, internal pulldown disabled	-500		+500	nA
Input Pullup Resistor to RSTN	R_{PU_VDD}	Pullup to $V_{DD} = V_{RST}$, RSTN at V_{IH}		18.7		k Ω
		Pullup to $V_{DD} = 3.63\text{V}$, RSTN at V_{IH}		10.0		
Input Pullup Resistor for All GPIO	R_{PU}	Device pin configured as GPIO, pullup to $V_{DD} = V_{RST}$, device pin at V_{IH}		18.7		k Ω
		Device pin configured as GPIO, pullup to $V_{DD} = 3.63\text{V}$, device pin at V_{IH}		10.0		
Input Pulldown Resistor for All GPIO	R_{PD}	Device pin configured as GPIO, pulldown to V_{SS} , $V_{DD} = V_{RST}$, device pin at V_{IL}		17.6		k Ω
		Device pin configured as GPIO, pulldown to V_{SS} , $V_{DD} = 3.63\text{V}$, device pin at V_{IL}		8.8		
CLOCKS						
System Clock Frequency	f_{SYS_CLK}				100	MHz
System Clock Period	t_{SYS_CLK}			$\frac{1}{f_{SYS_CLK}}$		μs
Internal Primary Oscillator (IPO)	f_{IPO}	Default OVR = [10]		100		MHz
External RF Oscillator (XRFO)	f_{XRFO}	Required crystal characteristics: $C_L = 12\text{pF}$, $ESR \leq 50\Omega$, $C_0 \leq 7\text{pF}$, temperature stability $\pm 20\text{ppm}$, initial tolerance $\pm 20\text{ppm}$	14		32	MHz
Internal Baud Rate Oscillator (IBRO)	f_{IBRO}			7.3728		MHz
Internal Nano-Ring Oscillator (INRO)	f_{INRO}	Measured at $V_{DD} = 1.8\text{V}$		70		kHz
External RTC Oscillator (XRTCO)	f_{XRTCO}	32.768kHz watch crystal, $C_L = 6\text{pF}$, $ESR < 90\text{k}\Omega$, $C_0 < 2\text{pF}$		32.768		kHz
RTC Operating Current	I_{RTC}	All power modes, RTC enabled		0.35		μA

Electrical Characteristics (continued)

(Limits are 100% tested at $T_A = +25^\circ\text{C}$ and $T_A = +105^\circ\text{C}$. Limits over the operating temperature range and relevant supply voltage range are guaranteed by design and characterization. Specifications marked GBD are guaranteed by design and not production tested. Specifications to the minimum operating temperature are guaranteed by design and are not production tested.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
RTC Power-Up Time	$t_{\text{RTC_ON}}$			250		ms
External Clock Input Frequency	$f_{\text{EXT_CLK}}$	EXT_CLK1 selected			50	MHz
		EXT_CLK2 selected			1	
FLASH MEMORY						
Flash Erase Time	$t_{\text{M_ERASE}}$	Mass erase		30		ms
	$t_{\text{P_ERASE}}$	Page erase		30		
Flash Programming Time Per Word	t_{PROG}	32-bit programming mode, $f_{\text{FLC_CLK}} = 1\text{MHz}$		42		μs
Flash Endurance			10			kcycles
Data Retention	t_{RET}	$T_A = +125^\circ\text{C}$	10			years

Electrical Characteristics—SPI

(Timing specifications are guaranteed by design and not production tested.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
MASTER MODE						
SPI Master Operating Frequency	f_{MCK}	$f_{\text{SYS_CLK}} = 100\text{MHz}$, $f_{\text{MCK(MAX)}} = f_{\text{SYS_CLK}}/2$			50	MHz
SPI Master SCK Period	t_{MCK}			$1/f_{\text{MCK}}$		ns
SCK Output Pulse-Width High/Low	t_{MCH} , t_{MCL}		$t_{\text{MCK}}/2$			ns
MOSI Output Hold Time After SCK Sample Edge	t_{MOH}		$t_{\text{MCK}}/2$			ns
MOSI Output Valid to Sample Edge	t_{MOV}		$t_{\text{MCK}}/2$			ns
MOSI Output Hold Time After SCK Low Idle	t_{MLH}			$t_{\text{MCK}}/2$		ns
MISO Input Valid to SCK Sample Edge Setup	t_{MIS}			5		ns
MISO Input to SCK Sample Edge Hold	t_{MIH}			$t_{\text{MCK}}/2$		ns
SLAVE MODE						
SPI Slave Operating Frequency	f_{SCK}				50	MHz
SPI Slave SCK Period	t_{SCK}			$1/f_{\text{SCK}}$		ns
SCK Input Pulse-Width High/Low	t_{SCH} , t_{SCL}			$t_{\text{SCK}}/2$		
SSx Active to First Shift Edge	t_{SSE}			10		ns

Electrical Characteristics—SPI (continued)

(Timing specifications are guaranteed by design and not production tested.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
MOSI Input to SCK Sample Edge Rise/Fall Setup	t_{SIS}			5		ns
MOSI Input from SCK Sample Edge Transition Hold	t_{SIH}			1		ns
MISO Output Valid After SCLK Shift Edge Transition	t_{SOV}			5		ns
SCK Inactive to SSx Inactive	t_{SSD}			10		ns
SSx Inactive Time	t_{SSH}			$1/f_{SCK}$		μ s
MISO Hold Time After SSx Deassertion	t_{SLH}			10		ns

Electrical Characteristics—I²C

(Timing specifications are guaranteed by design and not production tested.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
STANDARD MODE						
Output Fall Time	t_{OF}	Standard mode, from $V_{IH(MIN)}$ to $V_{IL(MAX)}$		150		ns
SCL Clock Frequency	f_{SCL}		0		100	kHz
Low Period SCL Clock	t_{LOW}		4.7			μ s
High Time SCL Clock	t_{HIGH}		4.0			μ s
Setup Time for Repeated Start Condition	$t_{SU;STA}$		4.7			μ s
Hold Time for Repeated Start Condition	$t_{HD;STA}$		4.0			μ s
Data Setup Time	$t_{SU;DAT}$			300		ns
Data Hold Time	$t_{HD;DAT}$			10		ns
Rise Time for SDA and SCL	t_R			800		ns
Fall Time for SDA and SCL	t_F			200		ns
Setup Time for a Stop Condition	$t_{SU;STO}$		4.0			μ s
Bus Free Time Between a Stop and Start Condition	t_{BUS}		4.7			μ s
Data Valid Time	$t_{VD;DAT}$		3.45			μ s
Data Valid Acknowledge Time	$t_{VD;ACK}$		3.45			μ s

Electrical Characteristics—I²C (continued)

(Timing specifications are guaranteed by design and not production tested.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
FAST MODE						
Output Fall Time	t _{OF}	From V _{IH(MIN)} to V _{IL(MAX)}		150		ns
Pulse Width Suppressed by Input Filter	t _{SP}			75		ns
SCL Clock Frequency	f _{SCL}		0		400	kHz
Low Period SCL Clock	t _{LOW}		1.3			μs
High Time SCL Clock	t _{HIGH}		0.6			μs
Setup Time for Repeated Start Condition	t _{SU;STA}		0.6			μs
Hold Time for Repeated Start Condition	t _{HD;STA}		0.6			μs
Data Setup Time	t _{SU;DAT}			125		ns
Data Hold Time	t _{HD;DAT}			10		ns
Rise Time for SDA and SCL	t _R			30		ns
Fall Time for SDA and SCL	t _F			30		ns
Setup Time for a Stop Condition	t _{SU;STO}		0.6			μs
Bus Free Time Between a Stop and Start Condition	t _{BUS}		1.3			μs
Data Valid Time	t _{VD;DAT}		0.9			μs
Data Valid Acknowledge Time	t _{VD;ACK}		0.9			μs
FAST MODE PLUS						
Output Fall Time	t _{OF}	From V _{IH(MIN)} to V _{IL(MAX)}		80		ns
Pulse Width Suppressed by Input Filter	t _{SP}			75		ns
SCL Clock Frequency	f _{SCL}		0		1000	kHz
Low Period SCL Clock	t _{LOW}		0.5			μs
High Time SCL Clock	t _{HIGH}		0.26			μs
Setup Time for Repeated Start Condition	t _{SU;STA}		0.26			μs
Hold Time for Repeated Start Condition	t _{HD;STA}		0.26			μs
Data Setup Time	t _{SU;DAT}			50		ns
Data Hold Time	t _{HD;DAT}			10		ns
Rise Time for SDA and SCL	t _R			50		ns

Electrical Characteristics—I²C (continued)

(Timing specifications are guaranteed by design and not production tested.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Fall Time for SDA and SCL	t_F			30		ns
Setup Time for a Stop Condition	$t_{SU;STO}$		0.26			μ s
Bus Free Time Between a Stop and Start Condition	t_{BUS}		0.5			μ s
Data Valid Time	$t_{VD;DAT}$		0.45			μ s
Data Valid Acknowledge Time	$t_{VD;ACK}$		0.45			μ s

Electrical Characteristics—I²S Slave

(Timing specifications are guaranteed by design and not production tested.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Bit Clock Frequency	f_{BCLK}	96kHz LRCLK frequency			3.072	MHz
BCLK High Time	t_{WBCLKH}			0.5		$1/f_{BCLK}$
BCLK Low Time				0.5		$1/f_{BCLK}$
LRCLK Setup Time	t_{LRCLK_BLCK}			25		ns
Delay Time, BCLK to SD (Output) Valid	t_{BCLK_SDO}			12		ns
Setup Time for SD (Input)	t_{SU_SDI}			6		ns
Hold Time SD (Input)	t_{HD_SDI}			3		ns

GPIO Drive Strength: Note 1: When using a GPIO bias voltage of 2.97V, the drive current capability of the GPIO is 2x that of its drive strength when using a GPIO bias voltage of 1.71V.

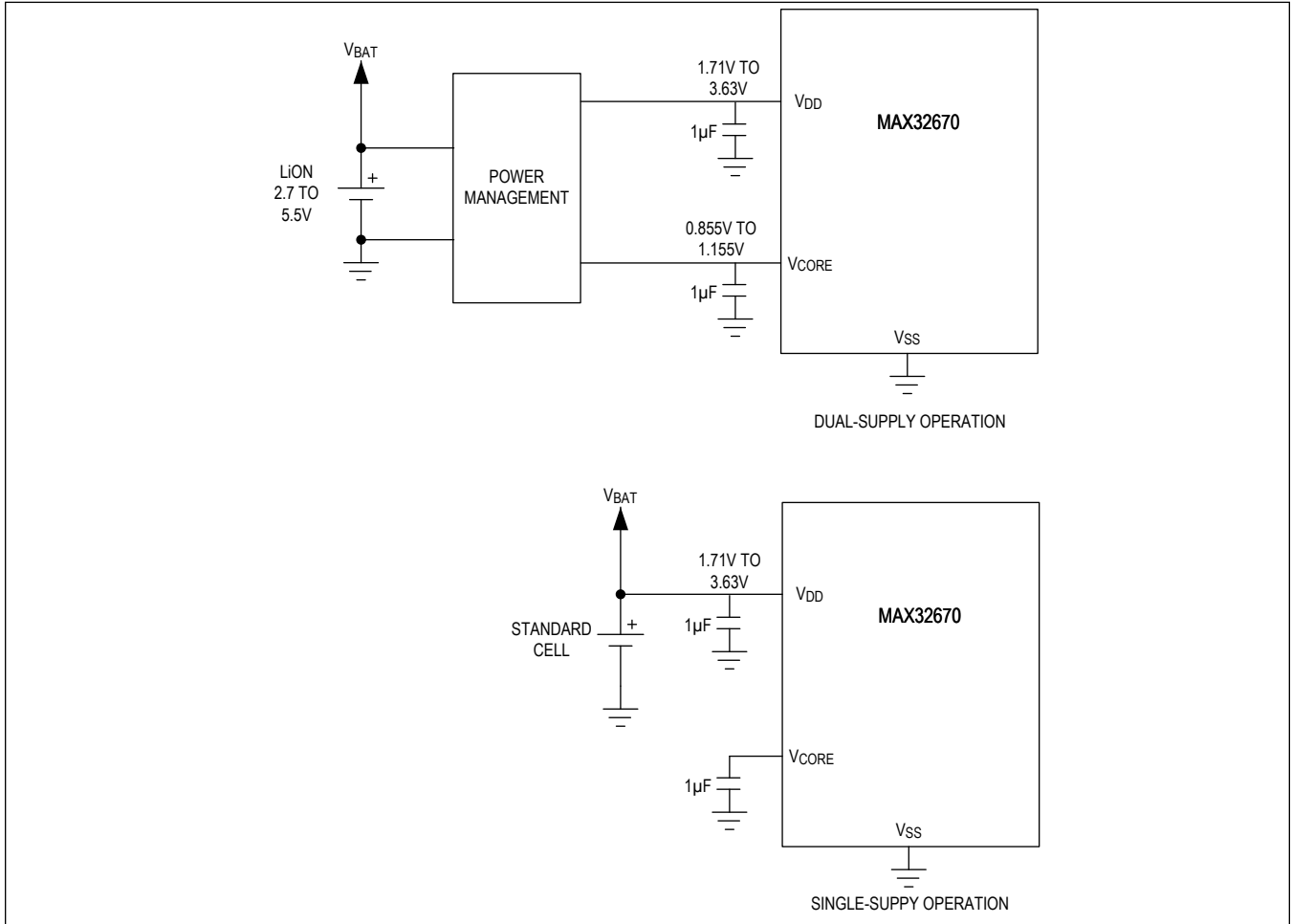


Figure 1. Power-Supply Operational Modes

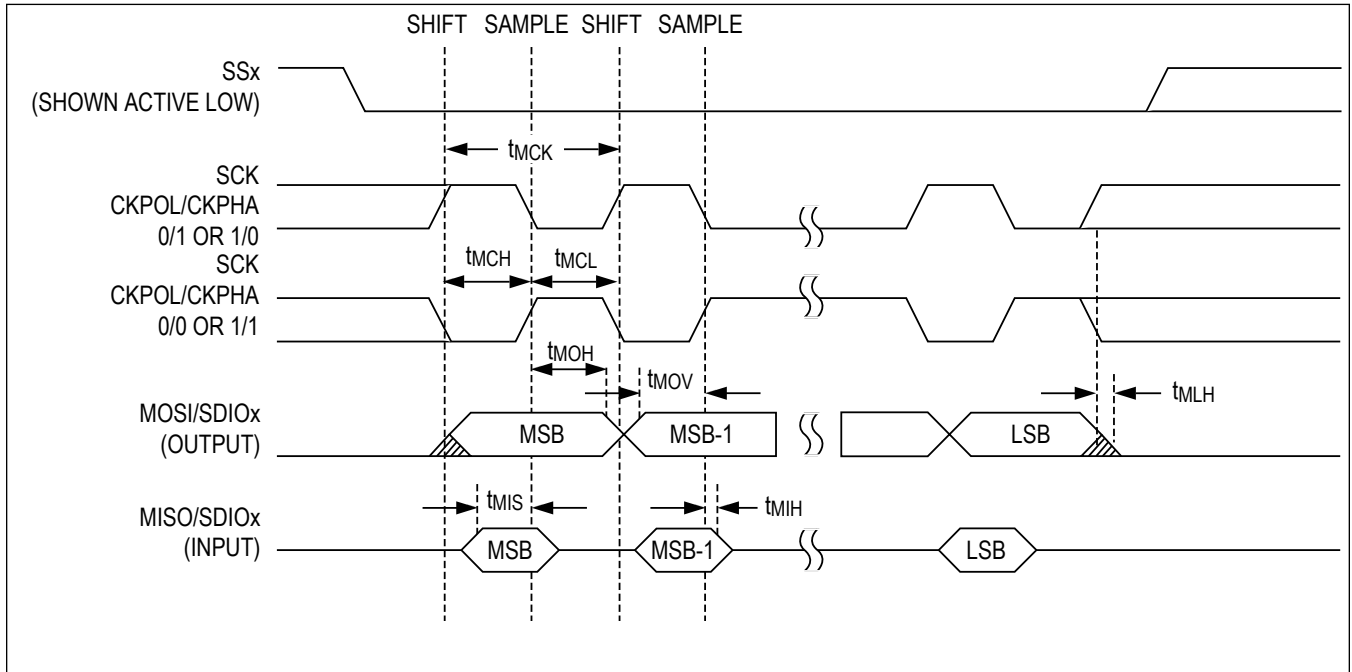


Figure 2. SPI Master Mode Timing Diagram

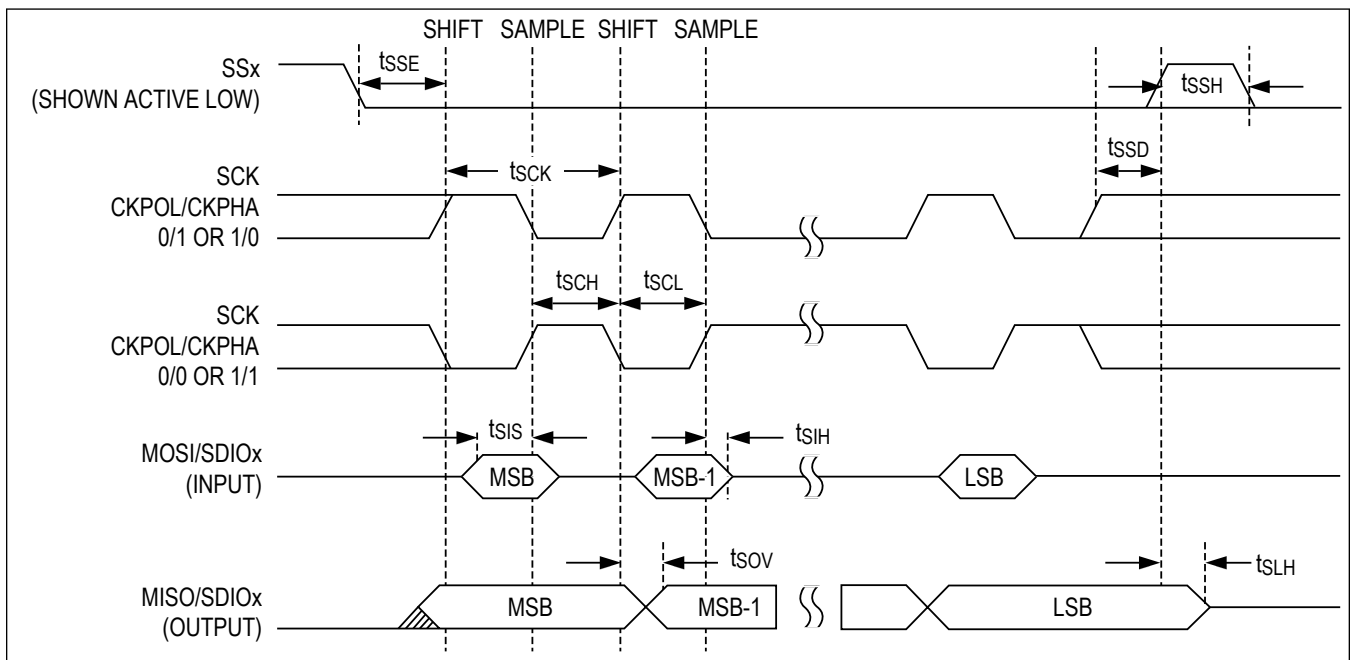


Figure 3. SPI Slave Mode Timing Diagram

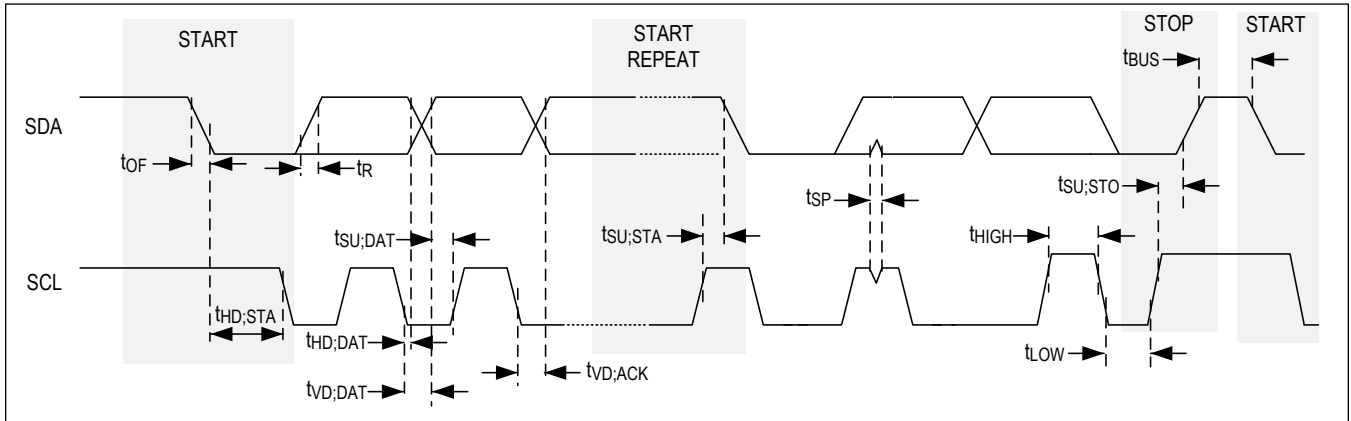


Figure 4. I²C Timing Diagram

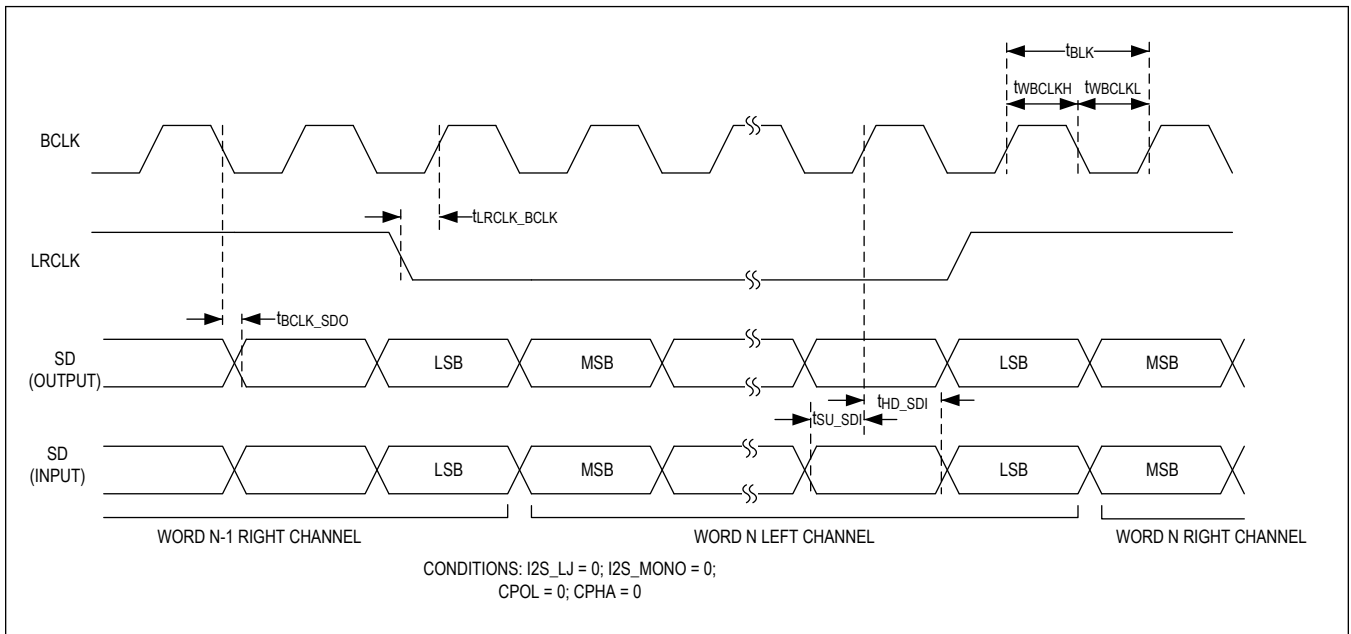
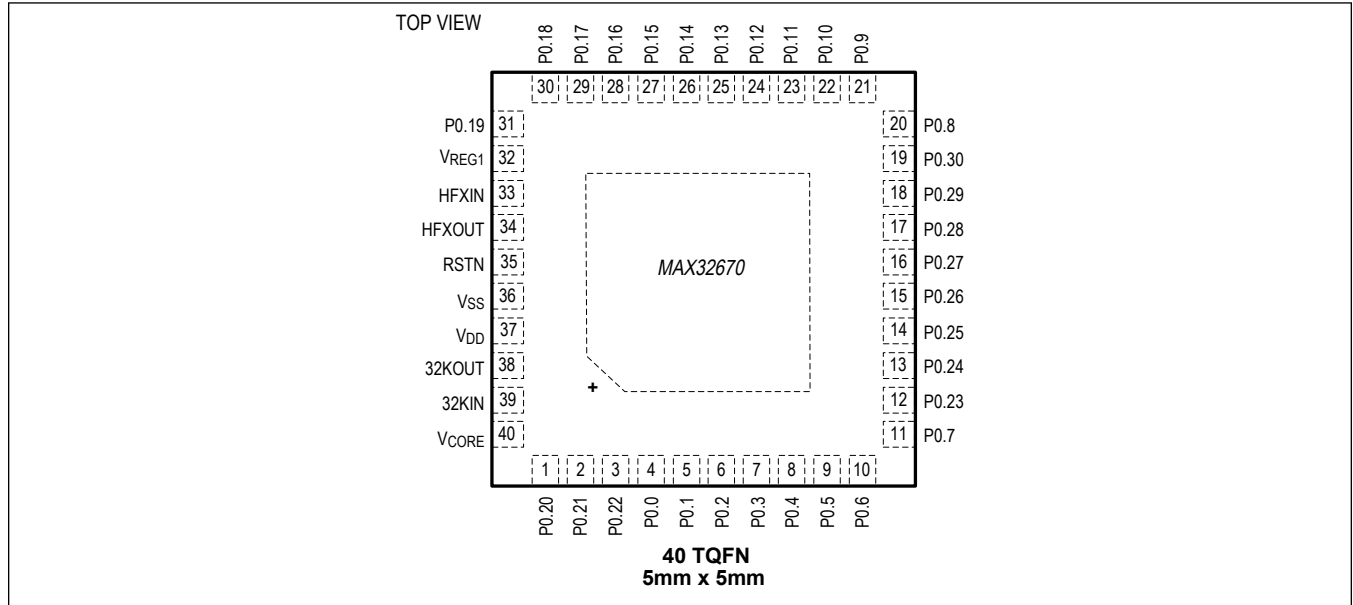


Figure 5. I²S Timing Diagram

Pin Configuration

40 TQFN



Pin Description

PIN	NAME	FUNCTION MODE					FUNCTION
		Primary Signal (Default)	Alternate Function 1	Alternate Function 2	Alternate Function 3	Alternate Function 4	
POWER (See the Applications Information section for bypass capacitor recommendations.)							
40	V _{CORE}	—	—	—	—	—	Digital Power-Supply Input. Bypass with 1x 100nf and 1x 1µF to V _{SS} .
32	V _{REG1}	—	—	—	—	—	Bypass with 4.7nF to V _{SS} . Do not connect this device pin to any other external circuitry.
37	V _{DD}	—	—	—	—	—	Power Supply Input. Bypass with 1.0µF and 100nF to V _{SS} .
36	V _{SS}	—	—	—	—	—	Digital Ground
RESET AND CONTROL							
35	RSTN	—	—	—	—	—	Active-Low, External System Reset Input. The device remains in reset while this pin is in its active state. When the pin transitions to its inactive state, the device performs a POR reset (resetting all logic on all supplies except for real-time clock circuitry) and begins execution. This pin has an internal pullup to the V _{DD} supply.

40 TQFN

PIN	NAME	FUNCTION MODE					FUNCTION
		Primary Signal (Default)	Alternate Function 1	Alternate Function 2	Alternate Function 3	Alternate Function 4	
CLOCK							
38	32KOUT	—	—	—	—	—	32kHz Crystal Oscillator Output
39	32KIN	—	—	—	—	—	32kHz Crystal Oscillator Input. Connect a 32kHz crystal between 32KIN and 32KOUT for RTC operation. Optionally, this pin can be configured as the input for an external CMOS-level clock source.
33	HFXIN	—	—	—	—	—	RF Crystal Oscillator Input. Connect the crystal between HFXIN and HFXOUT. Optionally, this pin can be configured as the input for an external square wave source. See the Electrical Characteristics table for details of the crystal requirements.
34	HFXOUT	—	—	—	—	—	RF Crystal Oscillator Output. Connect the crystal between HFXIN and HFXOUT. See the Electrical Characteristics table for details of the crystal requirements.
GPIO AND ALTERNATE FUNCTION (See the Applications Information section for GPIO and Alternate Function Matrices.)							
4	P0.0	P0.0	SWDIO	—	TMR0A_I	—	Single-Wire Debug I/O; Timer 0 Port Map A Input
5	P0.1	P0.1	SWDCLK	—	TMR0A_O	—	Single-Wire Debug Clock; Timer 0 Port Map A Output
6	P0.2	P0.2	SPI0_MISO	UART1B_RX	TMR1A_I	—	SPI0 Master In Slave Out; UART 1 Port Map B RX; Timer 1 Port Map A Input
7	P0.3	P0.3	SPI0_MOSI	UART1B_TX	TMR1A_O	—	SPI0 Master Out Slave In; UART 1 Port Map B TX; Timer 1 Port Map A Output
8	P0.4	P0.4	SPI0_SCK	UART1B_CTS	TMR2A_I	—	SPI0 Serial Clock; UART 1 Port Map B CTS; Timer 2 Port Map A Input
9	P0.5	P0.5	SPI0_SS0	UART1B_RTS	TMR2A_O	DIV_CLK_OUTA	SP0 Slave Select 0; UART 1 Port Map B RTS; Timer 2 Port Map A Output; Divided Clock Output Port Map A
10	P0.6	P0.6	I2C0_SCL	LPTMR0_I	TMR3A_I	—	I2C0 Serial Clock; Low Power Timer 0 Input; Timer 3 Port Map A Input
11	P0.7	P0.7	I2C0_SDA	LPTMR0_O	TMR3A_O	—	I2C0 Serial Data; Low Power Timer 0 Output; Timer 3 Port Map A Output
20	P0.8	P0.8	UART0A_RX	I2S0_SDO	TMR0B_I	—	UART 0 Port Map A Rx; I2S0 Serial Data Output; Timer 0 Port Map B Input

40 TQFN

PIN	NAME	FUNCTION MODE					FUNCTION
		Primary Signal (Default)	Alternate Function 1	Alternate Function 2	Alternate Function 3	Alternate Function 4	
21	P0.9	P0.9	UART0A_TX	I2S0_LRCLK	TMR0B_O	—	UART 0 Port Map A Tx; I2S0 Left/Right Clock; Timer 0 Port Map B Output
22	P0.10	P0.10	UART0A_CTS	I2S0_BCLK	TMR1B_I	DIV_CLK_OUTB	UART 0 Port Map A CTS; I2S0 Bit Clock; Timer 1 Port Map B Input; Divided Clock Output Port Map B
23	P0.11	P0.11	UART0A_RTS	I2S0_SDI	TMR1B_O	—	UART 0 Port Map A RTS; I2S0 Serial Data Input; Timer 1 Port Map B Output
24	P0.12	P0.12	I2C1_SCL	EXT_CLK2	TMR2B_I	EXT_CLK1	I2C1 Serial Clock; Low Power External Clock Input; Timer 2 Port Map B Input; External Clock Input
25	P0.13	P0.13	I2C1_SDA	32KCAL	TMR2B_O	SPI1_SS0	I2C1 Serial Data; 32.768kHz Calibration Output; Timer 2 Port Map B Output; SPI1 Slave Select 0
26	P0.14	P0.14	SPI1_MISO	UART2B_RX	TMR3B_I	—	SPI1 Master In Slave Out; UART 2 Port Map B RX; Timer 3 Port Map B Input
27	P0.15	P0.15	SPI1_MOSI	UART2B_TX	TMR3B_O	—	SPI1 Master Out Slave In; UART 2 Port Map B TX; Timer 3 Port Map B Output
28	P0.16	P0.16	SPI1_SCK	UART2B_CTS	TMR0C_I	—	SPI1 Serial Clock; UART 2 Port Map B CTS; Timer 0 Port Map C Input
29	P0.17	P0.17	SPI1_SS0	UART2B_RTS	TMR0C_O	—	SPI1 Slave Select 0; UART 2 Port Map B RTS; Timer 0 Port Map C Output
30	P0.18	P0.18	I2C2_SCL	—	TMR1C_I	—	I2C2 Serial Clock; Timer 1 Port Map C Input
31	P0.19	P0.19	I2C2_SDA	—	TMR1C_O	—	I2C2 Serial Data; Timer 1 Port Map C Output
1	P0.20	P0.20	CM4_RX	—	TMR2C_I	SWDCLKB	CM4 Rx Event Input; Timer 2 Port Map C Input; Single-Wire Debug Clock Port Map B
2	P0.21	P0.21	CM4_TX	—	TMR2C_O	—	CM4 Tx Event Output; Timer 2 Port Map C Output
3	P0.22	P0.22	LPTMR1_I	—	TMR3C_I	SWDIOB	Low-Power Timer 1 Input; Timer 3 Port Map C Input; Single-Wire Debug Port Map B I/O
12	P0.23	P0.23	LPTMR1_O	—	TMR3C_O	—	Low-Power Timer 1 Output; Timer 3 Port Map C Output
13	P0.24	P0.24	LPUART0_CTS	UART0B_RX	TMR0D_I	—	Low-Power UART 0 CTS; UART0 Port Map B Rx; Timer 0 Port Map D Input

40 TQFN

PIN	NAME	FUNCTION MODE					FUNCTION
		Primary Signal (Default)	Alternate Function 1	Alternate Function 2	Alternate Function 3	Alternate Function 4	
14	P0.25	P0.25	LPUART0_RTS	UART0B_TX	TMR0D_O	—	Low-Power UART 0 RTS; UART 0 Port Map B Tx; Timer 0 Port Map D Output
15	P0.26	P0.26	LPUART0_RX	UART0B_CTS	TMR1D_I	—	Low-Power UART 0 Rx; UART 0 Port Map B CTS; Timer 1 Port Map D Input
16	P0.27	P0.27	LPUART0_TX	UART0B_RTS	TMR1D_O	—	Low-Power UART 0 Tx; UART 0 Port Map B RTS; Timer 1 Port Map D Output
17	P0.28	P0.28	UART1A_RX	—	TMR2D_I	—	UART 1 Port Map A Rx; Timer 2 Port Map D Input
18	P0.29	P0.29	UART1A_TX	—	TMR2D_O	—	UART 1 Port Map A Tx; Timer 2 Port Map D output
19	P0.30	P0.30	UART1A_CTS	—	TMR3D_I	—	UART 1 Port Map A CTS; Timer 3 Port Map D Input

Detailed Description

MAX32670

The MAX32670 is an ultra-low-power, cost-effective, high reliability 32-bit microcontroller enabling designs with complex sensor processing without compromising battery life. It combines a flexible and versatile power management unit with the powerful Arm Cortex-M4 processor with FPU. It also offers legacy designs an easy and cost optimal upgrade path from 8- or 16-bit microcontrollers. Error correction coding (ECC) (single error correction double error detection) for both flash and SRAM provides extremely reliable code execution. The device integrates up to 384KB of flash memory and 160KB (128KB with ECC) of SRAM to accommodate application and sensor code.

The device features five powerful and flexible power modes. It can operate from a single-supply battery or a dual-supply typically provided by a PMIC. The I²C ports support standard, fast, fast-plus, and high-speed modes, operating up to 3400kbps. The SPI ports can run up to 50MHz in both master and slave mode, and three UARTs can run up to 4000kbaud. One low power UART can run up to 1000kbaud. Four general-purpose 32-bit timers, two low power 32-bit timers, two windowed watchdog timers, and a real-time clock are also provided. An I²S interface provides digital audio streaming to a codec.

Arm Cortex-M4 Processor with FPU Engine

The Arm Cortex-M4 processor with FPU combines high-efficiency signal processing functionality with low power, low cost, and ease of use.

The Arm Cortex-M4 processor with FPU supports single instruction multiple data (SIMD) path DSP extensions, providing:

- Four parallel 8-bit add/sub
- Floating point single precision
- Two parallel 16-bit add/sub
- Two parallel MACs
- 32- or 64-bit accumulate
- Signed, unsigned, data with or without saturation

Memory

Internal Flash Memory

384KB of internal flash memory with error correction provides nonvolatile storage of program and data memory.

Internal SRAM

The internal 160KB SRAM provides low-power retention of application information in all power modes except STORAGE. For enhanced system reliability the SRAM can be configured as 128KB with error correction coded (ECC) single error correction-double error detection (SED-DED). The SRAM can be divided into granular banks that create a flexible SRAM retention architecture. This data retention feature is optional, and is configurable. This granularity allows the application to minimize its power consumption by only retaining the most essential data.

Clocking Scheme

Multiple clock sources can be selected as the system clock:

- Internal primary oscillator (IPO) at a nominal frequency of 100MHz
- Internal nano-ring oscillator at 80kHz
- External RTC oscillator at 32.768kHz (ERTCO) (external crystal required)
- Internal baud rate oscillator at 7.3728MHz (IBRO)
- External RF oscillator at 14MHz-32MHz (ERFO) (external crystal required)
- External square wave clock up to 50MHz
- External square wave clock up to 1MHz for LPTMR0, LPTMR1, and LPUART

An external 32.768kHz timebase is required when using the RTC.

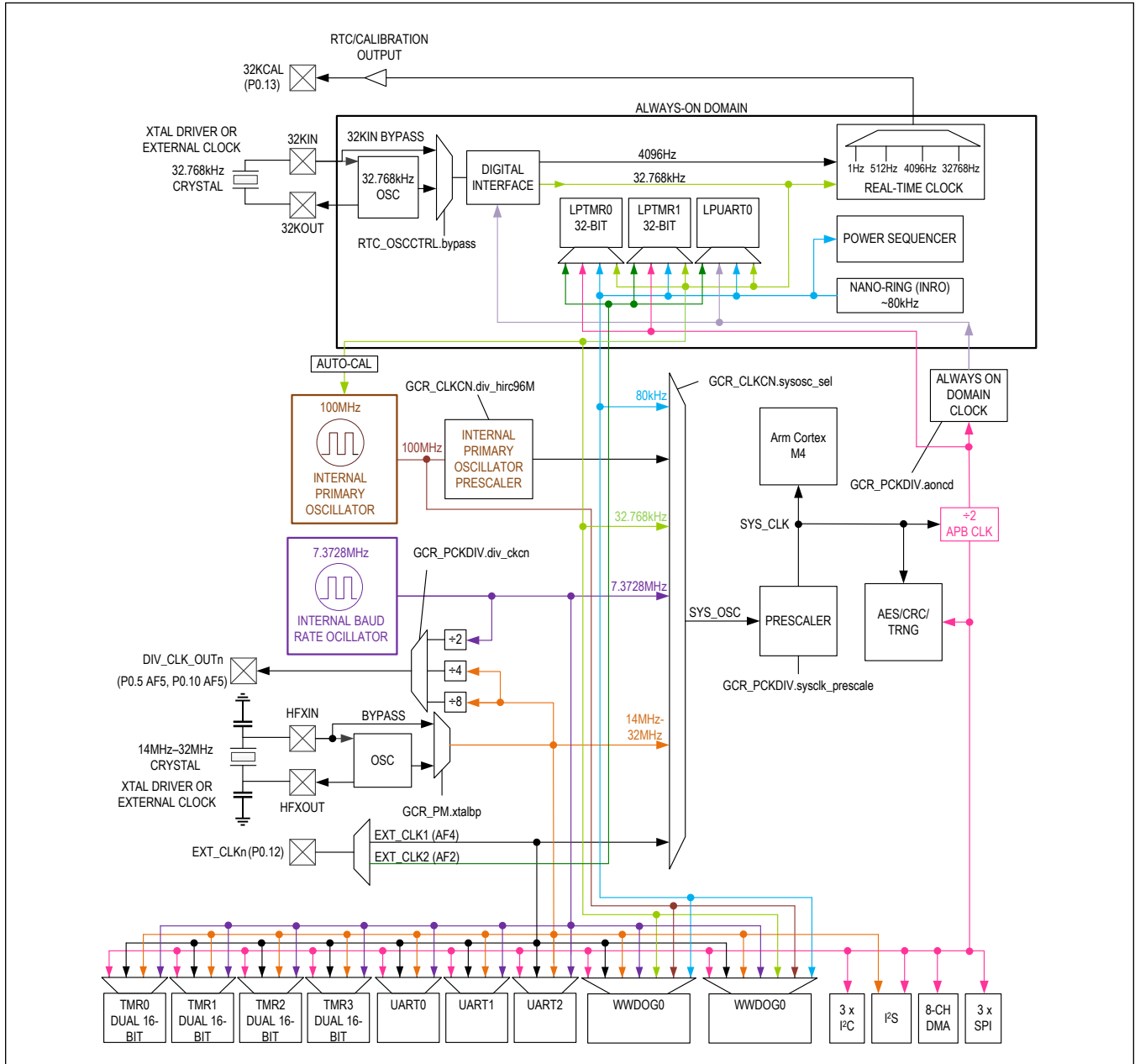


Figure 6. Clocking Scheme

General-Purpose I/O and Special Function Pins

Most general-purpose I/O (GPIO) pins share both a firmware-controlled I/O function and one or more special function signals associated with peripheral modules. Pins can be individually enabled for GPIO or peripheral special function use. Configuring a pin as a special function usually supersedes its use as a firmware-controlled I/O. Though this multiplexing between peripheral and GPIO functions is usually static, it can also be done dynamically. The electrical characteristics of a GPIO pin are identical whether the pin is configured as an I/O or special function, except where explicitly noted in the

[Electrical Characteristics](#) tables.

In GPIO mode, each pin of a port has an interrupt function that can be independently enabled and configured as a level- or edge-sensitive interrupt. All GPIOs share the same interrupt vector. Some packages do not have all of the GPIOs available.

When configured as GPIOs, the following features are provided. These features can be independently enabled or disabled on a per-pin basis.

- Configurable as input, output, bidirectional, or high-impedance
- Optional internal pullup resistor or internal pulldown resistor when configured as input
- Exit from low-power modes on rising or falling edge
- Selectable standard- or high-drive modes

The MAX32670 provides up to 31 GPIOs for the 40-pin TQFN.

Standard DMA Controller

The standard direct memory access (DMA) controller provides a means to off-load the CPU for memory/peripheral data transfer leading to a more power-efficient system. It allows automatic one-way data transfer between two entities. These entities can be either memories or peripherals. The transfers are done without using CPU resources. The following transfer modes are supported:

- 8 channel
- Peripheral to data memory
- Data memory to peripheral
- Data memory to data memory
- Event support

All DMA transactions consist of an AHB burst read into the DMA FIFO followed immediately by an AHB burst write from the FIFO.

Power Management

Power Management Unit

The power management unit (PMU) provides the optimal mix of high-performance and low-power consumption. It exercises intelligent, precise control of power distribution to the CPU and peripheral circuitry.

The PMU provides the following features:

- User-configurable system clock
- Automatic enabling and disabling of crystal oscillators based on power mode
- Multiple clock domains
- Fast wakeup of powered-down peripherals when activity detected

Active Mode

In this mode, the CPU is executing application code and all digital and analog peripherals are available on demand. Dynamic clocking disables local clocks in peripherals not in use. This mode corresponds to the Arm Cortex-M4 processor with FPU Active mode.

Sleep Mode

This mode allows for lower power consumption operation than active mode. The CPU is asleep, peripherals are on and the standard DMA block is available. The GPIO or any active peripheral can be configured to interrupt and cause transition to the Active mode. This mode corresponds to the Arm Cortex-M4 processor with FPU Sleep mode.

DeepSleep Mode

In this mode, CPU and critical peripheral configuration settings and all volatile memory are preserved.

The device status is as follows:

- CPU is powered down. System state and all SRAM is retained.
- The GPIO pins retain their state.
- The transition from DeepSleep to Active mode is faster than the transition from Backup mode because system initialization is not required.
- The system oscillators are all disabled to provide additional power savings over Sleep mode.
- LPUART0 and LPTMR0/1 can be active and are optional wake-up sources

This mode corresponds to the Arm Cortex-M4 with FPU DeepSleep mode.

Backup Mode

This mode places the CPU in a static, low-power state. Backup mode supports the same wake-up sources as DeepSleep mode.

The device status is as follows:

- CPU is powered down.
- SRAM retention as per [Table 1](#). Each of the RAM blocks can be retained.
- LPUART0 and LPTMR0/1 can be active and are optional wake-up sources.

Table 1. Backup Mode RAM Retention

RAM BLOCK	RAM SIZE WITHOUT ECC (KB)	RAM SIZE WITH ECC (KB)
SYSRAM0	20	16
SYSRAM1	20	16
SYSRAM2	40	32
SYSRAM3	80	64

Storage Mode

The device status is as follows:

- CPU is powered off.
- All peripherals are powered off.
- Wake-up from GPIO interrupt.
- RTC can be enabled.
- No SRAM retention.

Real-Time Clock

A real-time clock (RTC) keeps the time of day in absolute seconds. The 32-bit seconds register can count up to approximately 136 years and be translated to calendar format by application software.

The RTC provides a time-of-day alarm that can be programmed to any future value between 1 second and 12 days. When configured for long intervals, the time-of-day alarm can be used as a power-saving timer, allowing the device to remain in an extremely low-power mode, but still awoken periodically to perform assigned tasks. A second independent 32-bit 1/4096 subsecond alarm can be programmed between 244 μ s and 12 days. Both can be configured as recurring alarms. When enabled, either alarm can cause an interrupt or wake the device from most low power modes.

The time base is generated by a 32.768kHz crystal or an external clock source that must meet the electrical/timing requirements in the [Electrical Characteristics](#) table.

An RTC calibration feature provides the ability for user-software to compensate for minor variations in the RTC oscillator, crystal, temperature, and board layout. Enabling the 32KCAL alternate function outputs a timing signal derived from the RTC. External hardware can measure the frequency and adjust the RTC frequency in increments of ± 127 ppm with 1ppm resolution. Under most circumstances, the oscillator does not require any calibration.

Windowed Watchdog Timer (WWDT)

Microcontrollers are often used in harsh environments where electrical noise and electromagnetic interference (EMI) are

abundant. Without proper safeguards, these hazards can disturb device operation and corrupt program execution. One of the most effective countermeasures is the windowed watchdog timer (WWDT), which detects runaway code or system unresponsiveness.

The WWDT is a 32-bit, free-running counter with a configurable prescaler. When enabled, the WWDT must be periodically reset by the application software. Failure to reset the WWDT within the user-configurable timeout period indicates that the application software is not operating correctly and results in a WWDT timeout. A WWDT timeout can trigger an interrupt, system reset, or both. Either response forces the instruction pointer to a known good location before resuming instruction execution. The windowed timeout period feature provides more detailed monitoring of system operation, requiring the WWDT to be reset within a specific window of time.

The WWDT supports multiple clock option:

- 100MHz IPO
- 14MHz–32MHz ERFO (external crystal required)
- 7.3728MHz IBRO
- 80kHz INRO
- 32.768kHz ERTCO (external crystal required)
- External square wave clock up to 50MHz
- PCLK

The MAX32670 provides two instances of the windowed watchdog timer (WWDT0, WWDT1).

32-Bit Timer/Counter/PWM (TMR, LPTMR)

General-purpose, 32-bit timers provide timing, capture/compare, or generation of pulse-width modulated (PWM) signals with minimal software interaction.

The timer provides the following features:

- 32-bit up/down autoreload
- Programmable prescaler
- PWM output generation
- Capture, compare, and capture/compare capability
- External pin multiplexed with GPIO for timer input, clock gating or capture
- Timer output pin
- TMR0–TMR3 can be configured as 2 × 16-bit general-purpose timers
- Timer interrupt

The MAX32670 provides six 32-bit timers (TMR0, TMR1, TMR2, TMR3, LPTMR0, LPTMR1). LPTMR0 and LPTMR1 are capable of operation in the Low Power SLEEP, DEEPSLEEP, and BACKUP modes.

I/O functionality is supported for all of the timers. Note that the function of a port can be multiplexed with other functions on the GPIO pins, so it might not be possible to use all the ports depending on the device configuration. See [Table 2](#) for individual timer features.

Table 2. Timer Configuration Options

INSTANCE	SINGLE 32 BIT	DUAL 16 BIT	POWER MODE	CLOCK SOURCE							
				AOD_PCLK	PCLK	IBRO	ERFO	INRO	ERTCO	EXT_CLK1	EXT_CLK2
TMR0	YES	YES	ACTIVE SLEEP	NO	YES	YES	YES	NO	NO	YES	NO
TMR1	YES	YES	ACTIVE SLEEP	NO	YES	YES	YES	NO	NO	YES	NO
TMR2	YES	YES	ACTIVE SLEEP	NO	YES	YES	YES	NO	NO	YES	NO
TMR3	YES	YES	ACTIVE SLEEP	NO	YES	YES	YES	NO	NO	YES	NO

Table 2. Timer Configuration Options (continued)

LPTMR0	YES	NO	ACTIVE SLEEP	YES	NO	NO	NO	YES	YES	NO	YES
			DEEPSLEEP BACKUP	NO							
LPTMR1	YES	NO	ACTIVE SLEEP	YES	NO	NO	NO	YES	YES	NO	YES
			DEEPSLEEP BACKUP	NO							

Serial Peripherals

I²C Interface (I2C)

The I²C interface is a bidirectional, two-wire serial bus that provides a medium-speed communications network. It can operate as a one-to-one, one-to-many or many-to-many communications medium. These engines support standard-mode, fast-mode, fast-mode plus and high-speed mode I²C speeds. It provides the following features:

- Master or slave mode operation
 - Supports up to 4 different slave addresses in slave mode
- Supports standard 7-bit addressing or 10-bit addressing
- RESTART condition
- Interactive receive mode
- Tx FIFO preloading
- Support for clock stretching to allow slower slave devices to operate on higher speed busses
- Multiple transfer rates
 - Standard mode: 100kbps
 - Fast mode: 400kbps
 - Fast mode plus: 1000kbps
 - High-speed mode: 3400kbps
- Internal filter to reject noise spikes
- Receiver FIFO depth of 8 bytes
- Transmitter FIFO depth of 8 bytes

The MAX32670 provides three instances of the I²C peripheral (I2C0, I2C1, I2C2).

Serial Peripheral Interface (SPI)

The serial peripheral interface (SPI) is a highly configurable, flexible, and efficient synchronous interface among multiple SPI devices on a single bus. The bus uses a single clock signal and multiple data signals, and one or more slave select lines to address only the intended target device. The SPI operates independently and requires minimal processor overhead.

The provided SPI peripherals can operate in either slave or master mode and provide the following features:

- SPI modes 0, 1, 2, 3 for single-bit communication
- 3- or 4-wire mode for single-bit slave device communication
- Full-duplex operation in single-bit, 4-wire mode
- Multimaster mode fault detection
- Programmable interface timing
- Programmable SCK frequency and duty cycle
- 32-byte transmit and receive FIFOs
- Slave select assertion and deassertion timing with respect to leading/trailing SCK edge

The MAX32670 provides three instances of the SPI peripheral (SPI0, SPI1, SPI2). See [Table 3](#) for configuration options.

Table 3. SPI Configuration Options

INSTANCE	DATA	SLAVE SELECT LINES	MAXIMUM FREQUENCY MASTER MODE (MHz)	MAXIMUM FREQUENCY SLAVE MODE (MHz)
		40TQFN		
SPI0	3 wire, 4 wire	1	50	50
SPI1	3 wire, 4 wire	1	50	50
SPI2	3 wire, 4 wire	1	50	50

I²S Interface (I2S)

The I²S interface is a bidirectional, four-wire serial bus that provides serial communications for codecs and audio amplifiers compliant with the I²S Bus Specification, June 5, 1996. It provides the following features:

- Master and Slave mode operation
- Support for 4 channels
- 8, 16, 24, and 32 bit frames
- Receive and transmit DMA support
- Wakeup on FIFO status (full/empty/threshold)
- Pulse Density Modulation support for receive channel
- Word select polarity control
- First bit position selection
- Interrupts generated for FIFO status
- Receiver FIFO depth of 32 bytes
- Transmitter FIFO depth of 32 bytes

The MAX32670 provides one instance of the I²S peripheral (I2S0).

UART (UART, LPUART)

The universal asynchronous receiver-transmitter (UART, LPUART) interface supports full-duplex asynchronous communication with optional hardware flow control (HFC) modes to prevent data overruns. If HFC mode is enabled on a given port, the system uses two extra pins to implement the industry standard request to send (RTS) and clear to send (CTS) flow control signaling. Each instance is individually programmable.

- 2-wire interface or 4-wire interface with flow control
- 8-byte send/receive FIFO
- Full-duplex operation for asynchronous data transfers
- Interrupts available for frame error, parity error, CTS, Rx FIFO overrun and FIFO full/partially full conditions
- Automatic parity and frame error detection
- Independent baud-rate generator
- Programmable 9th-bit parity support
- Multidrop support
- Start/stop bit support
- Hardware flow control using RTS/CTS
- 4000kbaud for UART maximum baud rate
- 1000kbaud for LPUART maximum baud rate
- Two DMA channels can be connected (read and write FIFOs)
- Programmable word size (5 bits to 8 bits)

The MAX32670 provides 4 instances of the UART peripheral (UART0, UART1, UART2, LPUART0). LPUART0 is capable of operation in the Low Power SLEEP, DEEPSLEEP, and BACKUP modes. See [Table 4](#) for configuration options.

Table 4. UART Configuration Options

INSTANCE	POWER MODE	CLOCK SOURCE							
		AOD_PCLK	PCLK	IBRO	ERFO	INRO	ERTCO	EXT_CLK1	EXT_CLK2
UART0	ACTIVE	NO	YES	YES	YES	NO	NO	YES	NO
UART1	ACTIVE	NO	YES	YES	YES	NO	NO	YES	NO
UART2	ACTIVE	NO	YES	YES	YES	NO	NO	YES	NO
LPUART0	ACTIVE/SLEEP	YES	NO	NO	NO	YES	YES	NO	YES
	DEEPSLEEP/BACKUP	NO							

Security

AES

The dedicated hardware-based AES engine supports the following algorithms:

- AES-128
- AES-192
- AES-256

The AES keys are automatically generated by the engine and stored in dedicated flash to protect against tampering. Key generation and storage is transparent to the user.

True Random Number Generator (TRNG)

Random numbers are a vital part of a secure application, providing random numbers that can be used for cryptographic seeds or strong encryption keys to ensure data privacy.

Software can use random numbers to trigger asynchronous events that result in nondeterministic behavior. This is helpful in thwarting replay attacks or key search approaches. An effective true random number generator (TRNG) must be continuously updated by a high-entropy source.

The provided TRNG is continuously driven by a physically-unpredictable entropy source. It generates a 128-bit true random number in 128 system clock cycles.

The TRNG can support the system-level validation of many security standards such as FIPS 140-2, PCI-PED, and Common Criteria. Contact Maxim for details of compliance with specific standards.

CRC Module

A cyclic redundancy check (CRC) hardware module provides fast calculations and data integrity checks by application software. The CRC module supports the following polynomials:

- CRC-16-CCITT
- CRC-32 ($X^{32} + X^{26} + X^{23} + X^{22} + X^{16} + X^{12} + X^{11} + X^{10} + X^8 + X^7 + X^5 + X^4 + X^2 + X + 1$)

Secure Boot

The secure boot feature provides an authenticated boot from internal flash. The secure boot feature provides the following:

- Trusted boot authentication through HMAC-SHA256
- Programmable customer root key (CRK)
- Optional challenge/response gated entry

Debug and Development Interface (SWD)

The serial wire debug interface is used for code loading and ICE debug activities. All devices in mass production have the debugging/development interface enabled.

Applications Information

Bypass Capacitors

The proper use of bypass capacitors reduces noise generated by the IC into the ground plane. The [Pin Descriptions](#) table indicates which pins should be connected to bypass capacitors, and the appropriate ground plane.

It is recommended that one instance of a bypass capacitor should be connected to each pin/ball of the IC package. For example, if the [Pin Descriptions](#) table shows 4 device pins associated with voltage supply A, a separate capacitor should be connected to each pin for a total of 4 capacitors.

Capacitors should be placed as close as possible to their corresponding device pins. Pins which recommend more than one value of capacitor per pin should place them in parallel with the lowest value capacitor first, closest to the pin.

Ordering Information

PART	FLASH (KB)	SRAM (KB)	BOOT LOADER	SECURE BOOT	PIN-PACKAGE
MAX32670GTL+	384	160	YES	NO	40 TQFN
MAX32670GTL+T	384	160	YES	NO	40 TQFN
MAX32671GTL+*	384	160	YES	YES	40 TQFN
MAX32671GTL+T*	384	160	YES	YES	40 TQFN

T = Tape and reel. Full reel.

*Future product—contact factory for availability.

MAX32670

High Reliability, Ultra-Low Power Microcontroller
Powered by Arm Cortex M4 Processor with FPU
for Industrial and IoT

Revision History

REVISION NUMBER	REVISION DATE	DESCRIPTION	PAGES CHANGED
0	4/20	Initial release	—

For pricing, delivery, and ordering information, please visit Maxim Integrated's online storefront at <https://www.maximintegrated.com/en/storefront/storefront.html>.

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